

WSD30L65DN33

P-Channel MOSFET

General Description

The WSD30L65DN33 is the highest performance trench P-Channel MOSFET with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The WSD30L65DN33 meet the RoHS and Green Product requirement 100% E_{AS} guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

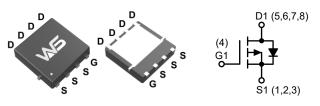
Product Summery

BVDSS	RDSON	ID
-30V	7.5mΩ	-50A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN3X3-8L Pin Configuration



Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±25	V
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ -10V ¹	-50	A
I₀@Tc=100°C	Continuous Drain Current, V _{GS} @ -10V ¹	-20	A
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ -10V ¹	-11.9	A
I _D @T _A =70℃	Continuous Drain Current, V _{GS} @ -10V ¹	-9.5	A
I _{DM}	Pulsed Drain Current ²	-150	A
E _{AS}	Single Pulse Avalanche Energy ³	54	mJ
I _{AS}	Avalanche Current	-33	A
P _D @T _C =25℃	Total Power Dissipation ⁴	35.7	W
P _D @T _A =25℃	Total Power Dissipation ⁴	2.08	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹		60	°C/W
R _{0JA}	Thermal Resistance Junction-Ambient 1 (t \leq 10s)		40	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹		3.5	°C/W

Absolute Maximum Ratings



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Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-30			V	
$\triangle BV_{DSS} / \triangle T_J$	BVDSS Temperature Coefficient	Reference to 25° C , I _D =-1mA		-0.0232		V/° C	
В	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-25A		7.5	9.5	mΩ	
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-15A		12	17		
V _{GS(th)}	Gate Threshold Voltage		-1.3	-1.8	-2.3	V	
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS} = V_{DS}$, $I_D = -2500A$		4.6		mV/℃	
	Drain Source Lookage Current	V_{DS} =-24V , V_{GS} =0V , T_{J} =25 $^{\circ}$ C			-1	- uA	
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-24V , V_{GS} =0V , T_{J} =85 $^{\circ}$ C			-30	uA	
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$			±100	nA	
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-30A		15		S	
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		8		Ω	
Qg	Total Gate Charge (-4.5V)	harge (-4.5V)		23.2			
Q _{gs}	Gate-Source Charge	V_{DS} =-15V , V_{GS} =-10V , I_{D} =-25A		7.5		nC	
Q _{gd}	Gate-Drain Charge			12.7			
T _{d(on)}	Turn-On Delay Time			12	22		
Tr	Rise Time V_{DD} =-15V , V_{GS} =-10V , R_G =6 Ω			13	23	20	
T _{d(off)}	Turn-Off Delay Time	I _D =-1Α ,RL=15Ω		62	112	ns	
T _f	Fall Time			101	182		
Ciss	Input Capacitance			2240	2910		
C _{oss}	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		465		pF	
C _{rss}	Reverse Transfer Capacitance			320			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}				-50	А
I _{DM}	Pulsed Source Current ^{2,6}	V _G =V _D =0V , Force Current			-150	А
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , TJ=25℃		-0.8	-1.2	V
t _{rr}	Reverse Recovery Time	IF=-25A,dI/dt=100A/µs, T,⊧=25℃		23		nS
Qrr	Reverse Recovery Charge	ii = 20/ ζαι/αι = 100/νμ3, 1j=20 C		10		nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t \leq 10 sec.

2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%

3. The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V, L=0.1mH, I_{AS} =-33A

4. The power dissipation is limited by 150°C junction temperature

5. The Min. value is 100% EAS tested guarantee.

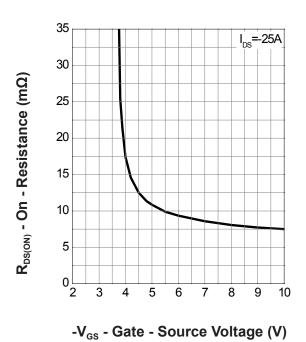
6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



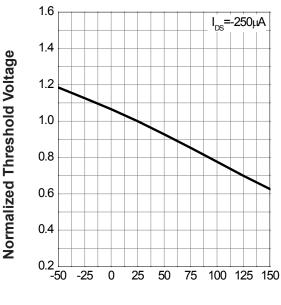
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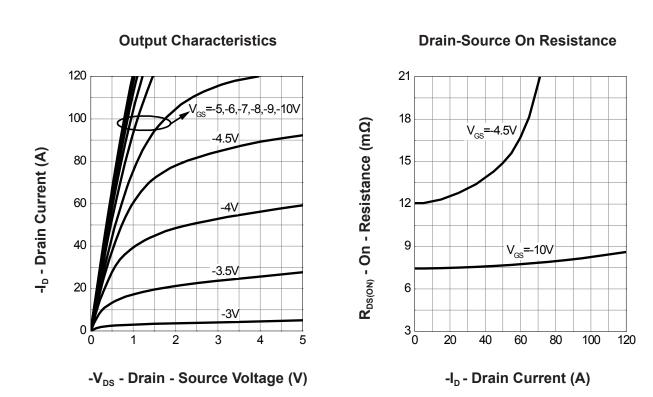
Typical Characteristics



Gate-Source On Resistance



T_j - Junction Temperature (°C)



Gate Threshold Voltage



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Typical Characteristics(Cont.)

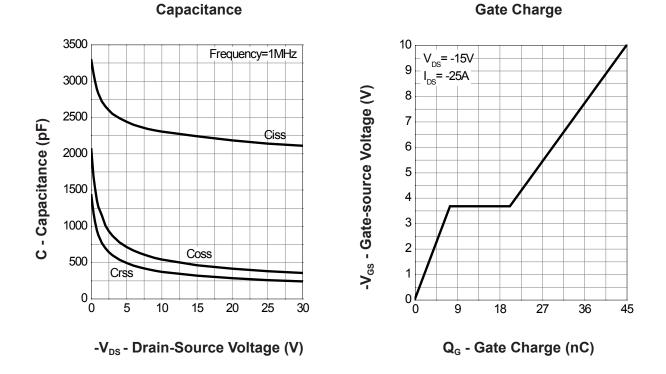


Fig.9 Normalized Maximum Transient Thermal Impedance

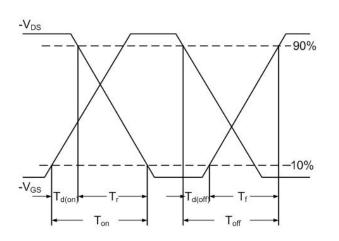
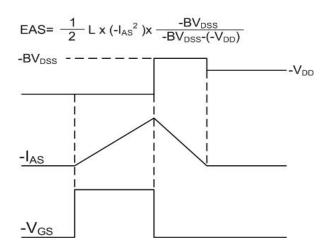


Fig.10 Switching Time Waveform



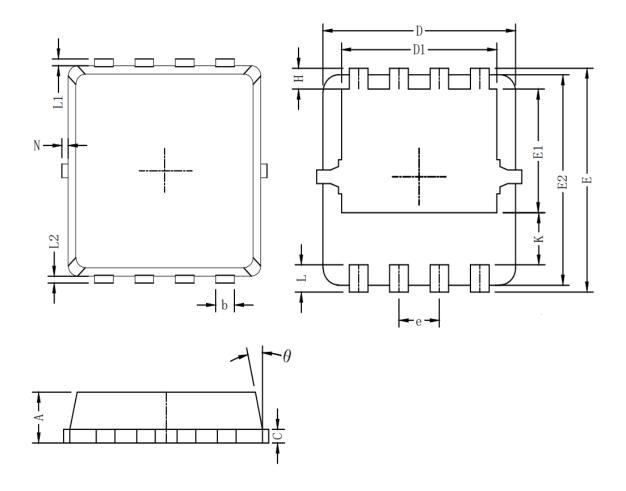




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Packaging information



Symbol	Dim in mm				
	min	typ	max		
А	0.6	0.75	0.9		
b	0.2	0.3	0.4		
С	0.15	0.2	0.25		
D	3	3.1	3.2		
D1	2.3	2.45	2.6		
E	3.15	3.3	3.45		
E1	1.43	1.73	1.93		
E2	2.9	3.05	3.2		
е	0.65BSC				
Н	0.2	0.35	0.5		
K	0.57	0.77	0.87		
L	0.3	0.4	0.5		
L1/L2	0.1REF				
θ	8°	10°	13°		
N	0		0.15		



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